

SEMICONDUCTOR DEVICE MANUFACTURING METHOD, SUBSTRATE PROCESSING
METHOD, SUBSTRATE PROCESSING DEVICE, AND PROGRAM

ABSTRACT

This technique comprises: a) a step of supplying a first precursor to a substrate, on a surface of which a first groundwork and a second groundwork are exposed, thereby causing a surface of the first groundwork to absorb at least some of the molecular structures of the molecules constituting the first precursor, thereby forming a first absorption inhibiting layer; b) a step of supplying a reactant to the substrate, thereby forming an absorption promoting layer on a surface of the second groundwork; c) a step of supplying a second precursor, the molecular structures of which are different from those of the first precursor, to the substrate, thereby causing a surface of the absorption promoting layer to absorb at least some of the molecular structures of the molecules constituting the second precursor, thereby forming a second absorption inhibiting layer; and d) a step of supplying a deposition substance to the substrate after the execution of the steps a), b) and c), thereby forming a film on the surface of the first groundwork.

[Representative Drawings]

FIGS. 4A to 4E